查询DFM600BXS17-A000供应商

KEY PARAMETERS

(typ)

(max)

(max)

V_{RRM}



DFM600BXS17-A000

Fast Recovery Diode Module

PDS5798-1.1 July 2004

FEATURES

- Low Reverse Recovery Charge
- High Switching Speed
- Low Forward Voltage Drop
- Isolated Base

APPLICATIONS

- Chopper Diodes
- Boost and Buck Converters
- Free-wheel Circuits
- Snubber Circuits
- Resonant Converters
- Multi-level Switch Inverters

The DFM600BXS17-A000 is a single 1700 volt, fast recovery diode (FRD) module. Designed for low power loss, the module is suitable for a variety of high voltage applications in motor drives and power conversion.

Fast switching times and low reverse recovery losses allow high frequency operation making the device suitable for the latest drive designs employing pwm and high frequency switching.

These modules incorporate electrically isolated base plates and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

ORDERING INFORMATION

Order As:

DFM600BXS17-A000

Note: When ordering, please use the complete part number.





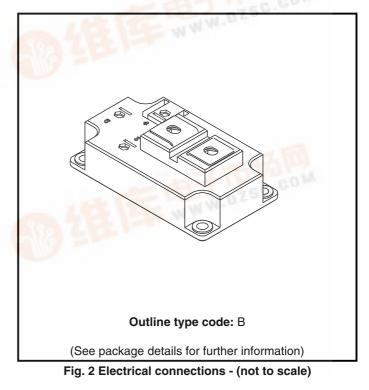
1700V

2.0V

600A

1200A

Fig. 1 Circuit diagram





ABSOLUTE MAXIMUM RATINGS

Stresses above those listed under 'Absolute Maximum Ratings' may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

T_{case} = 25°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
V _{RRM}	Repetitive peak reverse voltage	T _{vj} = 125°C	1700	V
I _F	Forward current (per arm)	DC, $T_{case} = 65^{\circ}C$, $T_{vj} = 125^{\circ}C$	600	A
I _{FM}	Max. forward current	$T_{case} = 110^{\circ}C, t_{p} = 1ms$	1200	A
I _{FSM}	Surge (non-repetitive) forward current		3674	А
l ² t	I ² t value fuse current rating	$V_{_{R}} = 0, t_{_{p}} = 10ms, T_{_{vj}} = 125^{\circ}C$	67.5	kA²s
Pmax	Maximum power dissipation	$T_{case} = 25^{\circ}C, T_{vj} = 125^{\circ}C$	2.0	kW
V _{isol}	Isolation voltage	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4	kV
Q_{pd}	Partial discharge	IEC1287. V ₁ = 1200V, V ₂ = 900V, 50Hz RMS	10	рС

THERMAL AND MECHANICAL RATINGS

Internal insulation:Al2O3Clearance:11mmBaseplate material:CuCTI (Critical Tracking Index):425Creepage distance:20mm

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
R _{th(j-c)}	Thermal resistance - diode (per arm)	Continuous dissipation -	-	-	50	°C/kW
		junction to case				
R _{th(c-h)}	Thermal resistance - case to heatsink	Mounting torque 5Nm	-	-	15	°C/kW
	(per module)	(with mounting grease)				
T _j	Junction temperature	-	-	-	125	°C
T _{stg}	Storage temperature range	-	-40	-	125	°C
-	Screw torque	Mounting - M6	3	-	5	Nm
		Electrical connections - M6	2.5	-	5	Nm



STATIC ELECTRICAL CHARACTERISTICS

$T_{v_i} = 25^{\circ}C$ unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
I _{RM}	Peak reverse current	V _R = 1200V, T _{vj} = 125°C	-	-	15	mA
V _F	Forward voltage	I _F = 600A	-	2.0	-	v
		I _F = 600A, T _{vj} = 125°C	-	2.05	-	v
L	Inductance (module)	-	-	20	-	nH

DYNAMIC ELECTRICAL CHARACTERISTICS

$T_{vi} = 25^{\circ}C$ unless stated otherwise.

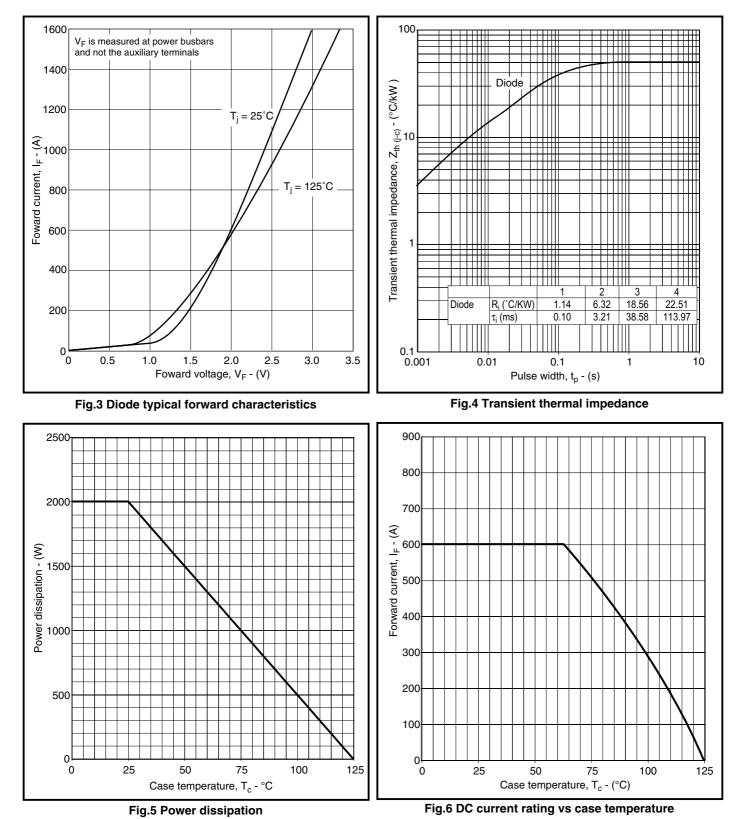
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
t _{rr}	Reverse recovery time	I _F = 600A,	-	1.4	-	μs
I _{rr}	Reverse recovery current	dI _F /dt = 4500A/µs,	-	345	-	А
Q _{rr}	Reverse recovery charge	V _R = 900V	-	150	-	μC
E _{rec}	Reverse recovery energy		-	105	-	mJ

T_{vj} = 125°C unless stated otherwise.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
t _{rr}	Reverse recovery time	I _F = 600A,	-	2.0	-	μs
I _{rr}	Reverse recovery current	dI _F /dt = 3800A/μs,	-	330	-	А
Q _{rr}	Reverse recovery charge	V _R = 900V	-	255	-	μC
E _{rec}	Reverse recovery energy		-	150	-	mJ



TYPICAL CHARACTERISTICS



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DFM600BXS17-A000

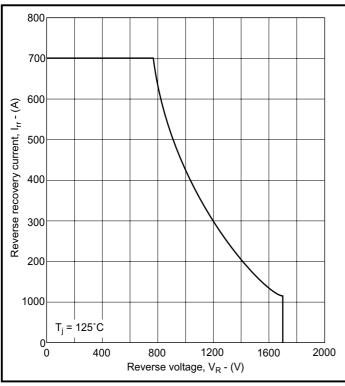
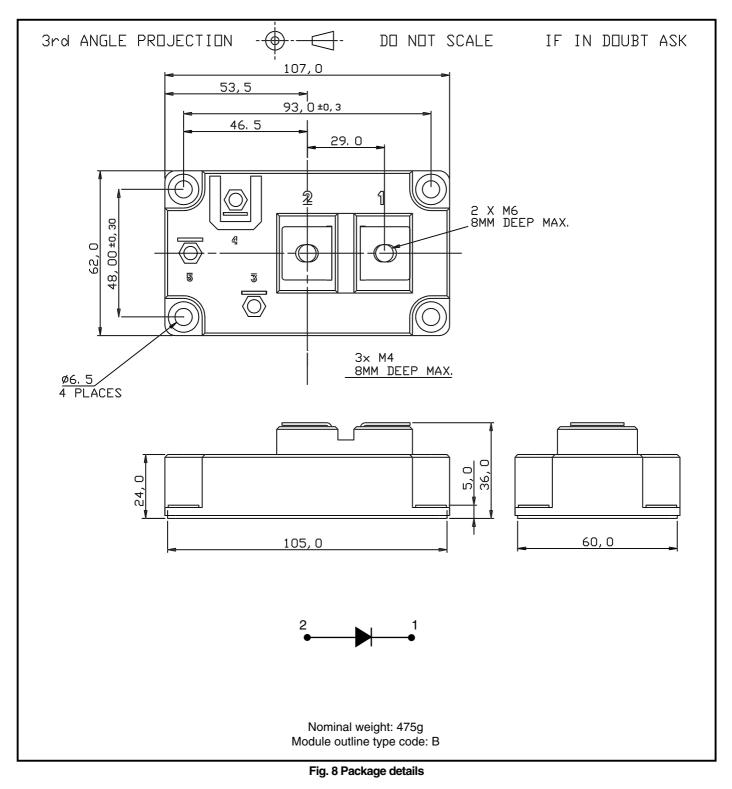


Fig.7 RBSOA



PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.





POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.



http://www.dynexsemi.com

e-mail: power_solutions@dynexsemi.com

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